

MJE270 (NPN), MJE271 (PNP)

Complementary Silicon Power Transistors

Features

- High Safe Operating Area
 $I_{S/B} @ 40 \text{ V}, 1.0 \text{ s} = 0.375 \text{ A}$
- Collector–Emitter Sustaining Voltage
 $V_{CEO(sus)} = 100 \text{ Vdc (Min)}$
- High DC Current Gain
 $h_{FE} @ 120 \text{ mA}, 10 \text{ V} = 1500 \text{ (Min)}$
- Pb–Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|----------------|--------------|--------------------------|
| Collector–Emitter Voltage | V_{CEO} | 100 | Vdc |
| Collector–Base Voltage | V_{CB} | 100 | Vdc |
| Emitter–Base Voltage | V_{EB} | 5.0 | Vdc |
| Collector Current – Continuous – Peak | I_C | 2.0 4.0 | Adc |
| Base Current | I_B | 0.1 | Adc |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 15 0.12 | W W/ $^\circ\text{C}$ |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 1.5 0.012 | W W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range | T_J, T_{stg} | –65 to +150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|--------------------|
| Thermal Resistance, Junction–to–Case | $R_{\theta JC}$ | 8.33 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction–to–Ambient | $R_{\theta JA}$ | 83.3 | $^\circ\text{C/W}$ |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

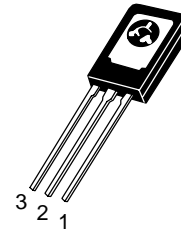
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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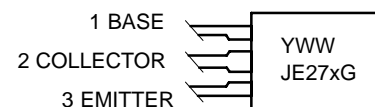
<http://onsemi.com>

**2.0 AMPERE
COMPLEMENTARY
POWER DARLINGTON
TRANSISTORS
100 VOLTS, 15 WATTS**



**TO-225
CASE 77
STYLE 3**

MARKING DIAGRAM



Y = Year
WW = Work Week
JE27x = Specific Device Code
x = 0 or 1
G = Pb–Free Package

ORDERING INFORMATION

| Device | Package | Shipping |
|---------|---------------------|---------------|
| MJE270 | TO–225 | 500 Units/Box |
| MJE270G | TO–225 (Pb–Free) | 500 Units/Box |
| MJE271 | TO–225 | 500 Units/Box |
| MJE271G | TO–225 (Pb–Free) | 500 Units/Box |

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|----------------|--------|-----|-----|------|
|----------------|--------|-----|-----|------|

OFF CHARACTERISTICS

| | | | | |
|---|----------------|-----|-----|------|
| Collector–Emitter Sustaining Voltage (Note 1) ($I_C = 10\text{ mAdc}$, $I_B = 0$) | $V_{CEO(sus)}$ | 100 | – | Vdc |
| Collector Cutoff Current ($V_{CE} = 100\text{ Vdc}$, $I_B = 0$) | I_{CEO} | – | 1.0 | mAdc |
| Collector Cutoff Current ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$) | I_{CBO} | – | 0.3 | mAdc |
| Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$) | I_{EBO} | – | 0.1 | mAdc |

SECOND BREAKDOWN

| | | | | |
|--|-----------|-----|---|-----|
| Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 40\text{ Vdc}$, $t = 1.0\text{ s}$, Non–repetitive) | $I_{S/b}$ | 375 | – | Adc |
|--|-----------|-----|---|-----|

ON CHARACTERISTICS (Note 1)

| | | | | |
|---|---------------|-------------|------------|-----|
| DC Current Gain ($I_C = 20\text{ mAdc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 120\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) | h_{FE} | 500 1500 | – – | – |
| Collector–Emitter Saturation Voltage ($I_C = 20\text{ mAdc}$, $I_B = 0.2\text{ mAdc}$) ($I_C = 120\text{ mAdc}$, $I_B = 1.2\text{ mAdc}$) | $V_{CE(sat)}$ | – – | 2.0 3.0 | Vdc |
| Base–Emitter On Voltage ($I_C = 120\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) | $V_{BE(on)}$ | – | 2.0 | Vdc |

DYNAMIC CHARACTERISTICS

| | | | | |
|--|-------|-----|---|-----|
| Current Gain – Bandwidth Product (Note 2) ($I_C = 0.05\text{ Adc}$, $V_{CE} = 5.0\text{ Vdc}$, $f_{test} = 1.0\text{ MHz}$) | f_T | 6.0 | – | MHz |
|--|-------|-----|---|-----|

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
2. $f_T = |h_{fe}| \cdot f_{test}$.

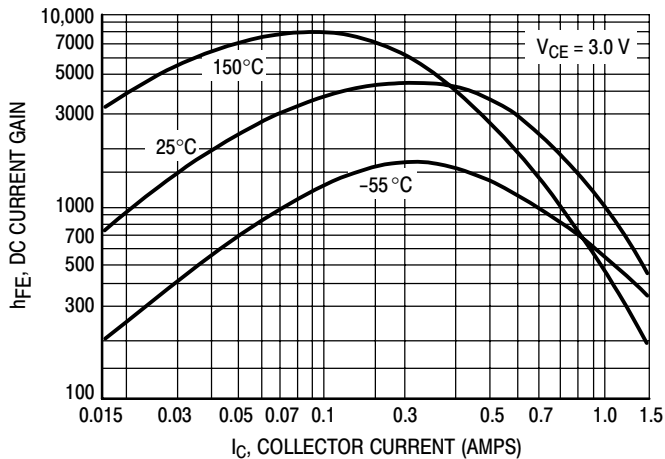


Figure 1. DC Current Gain

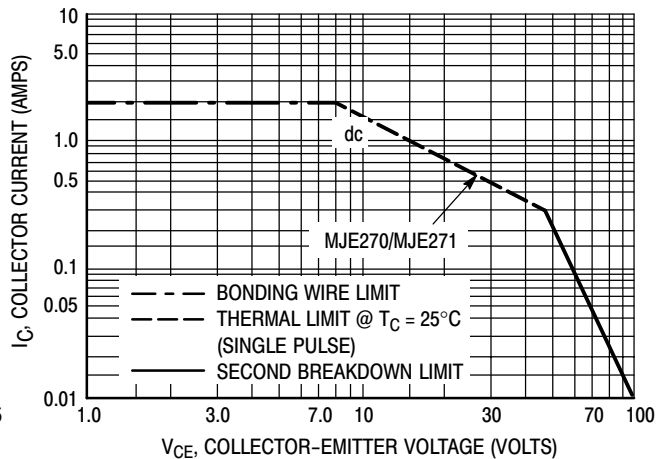
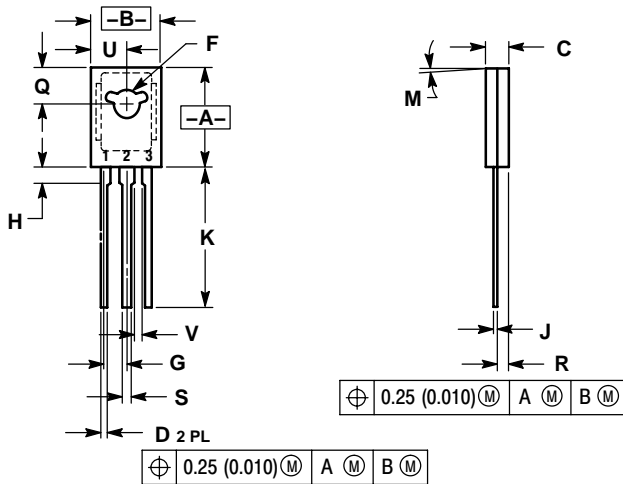


Figure 2. Safe Operating Area

MJE270 (NPN), MJE271 (PNP)

PACKAGE DIMENSIONS

TO-225
CASE 77-09
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.425 | 0.435 | 10.80 | 11.04 |
| B | 0.295 | 0.305 | 7.50 | 7.74 |
| C | 0.095 | 0.105 | 2.42 | 2.66 |
| D | 0.020 | 0.026 | 0.51 | 0.66 |
| F | 0.115 | 0.130 | 2.93 | 3.30 |
| G | 0.094 BSC | | 2.39 BSC | |
| H | 0.050 | 0.095 | 1.27 | 2.41 |
| J | 0.015 | 0.025 | 0.39 | 0.63 |
| K | 0.575 | 0.655 | 14.61 | 16.63 |
| M | 5° TYP | | 5° TYP | |
| Q | 0.148 | 0.158 | 3.76 | 4.01 |
| R | 0.045 | 0.065 | 1.15 | 1.65 |
| S | 0.025 | 0.035 | 0.64 | 0.88 |
| U | 0.145 | 0.155 | 3.69 | 3.93 |
| V | 0.040 | --- | 1.02 | --- |

STYLE 3:

1. BASE
2. COLLECTOR
3. EMITTER

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